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CONTENTS

Priority Communication

Aperiodic SiSn/Si multilayers for thermoelectric applications
A.A. Tonkikh, N.D. Zakharov, C. Eisenschmidt, H.S. Leipner and P. Werner 49

Classical semiconductors

Growth of InGaN/GaN core-shell structures on selectively etched GaN rods by molecular beam epitaxy

S. Albert, A. Bengoechea-Encabo, M. Sabido-Siller, M. Müller, G. Schmidt, S. Metzner, P. Veit, F. Bertram, M.A. Sánchez-García, J. Christen and E. Calleja 5

Growth temperature dependences of structural and electrical properties of Ga₂O₃ epitaxial films grown on β-Ga₂O₃ (010) substrates by molecular beam epitaxy

K. Sasaki, M. Higashiwaki, A. Kuramata, T. Masui and S. Yamakoshi 30

Investigation of single crystal 4H-SiC growth by the Solvent-Laser Heated Floating Zone technique

A.A. Woodworth, P.G. Neudeck, A. Sayir, F. Solá, M. Dudley and B. Raghothamachar 34

Germanium content and strain in Si_{1-x}Ge_x alloys characterized by Raman spectroscopy

D. Rouchon, M. Mermoux, F. Bertin and J.M. Hartmann 66

Optimization of power control in the reduction of basal plane dislocations during PVT growth of 4H-SiC single crystals

B. Gao and K. Kakimoto 92

Electronic materials

Effect of H₂ carrier gas on the physical properties of a GaN layer grown using Ga₂O vapor and NH₃

Y. Bu, M. Imade, A. Kitamoto, M. Yoshimura, M. Isemura and Y. Mori 1

Effects of dislocation strain on the epitaxy of lattice-mismatched AlGaInP layers

K. Mukherjee, D.A. Beaton, A. Mascarenhas, M.T. Bulsara and E.A. Fitzgerald 74

Solution growth; industrial biological and molecular crystallization

Copper oxide nanorods assembly and their whisker transformation at liquid-liquid interface and on solid surfaces

S.H. Al-Harathi, H.M. Widatallah, A.T. Al-Hinai, M.E. Elzain, H. Nishiyama and M.T.Z. Myint 41

Nitrogen doping of 4H-SiC by the top-seeded solution growth technique using Si-Ti solvent

K. Kusunoki, K. Kamei, K. Seki, S. Harada and T. Ujihara 60

Production method of carbamazepine/saccharin cocrystal particles by using two solution mixing based on the ternary phase diagram

S. Kudo and H. Takiyama 87

General subjects

Effect of (100) GaAs substrate misorientation on electrophysical parameters, structural properties and surface morphology of metamorphic HEMT nanoheterostructures InGaAs/InAlAs

G.B. Galiev, I.S. Vasil'evskii, E.A. Klimov, S.S. Pushkarev, A.N. Klochkov, P.P. Maltsev, M.Yu. Presniakov, I.N. Trunkin and A.L. Vasiliev 11

Germanium nanowire synthesis using solid precursors

B. Aksoy, Y.E. Kalay and H.E. Unalan 20

Formation of hollow bone-like morphology of calcium carbonate on surfactant/polymer templates

M.M.M.G.P.G. Mantilaka, H.M.T.G.A. Pitawala, R.M.G. Rajapakse, D.G.G.P. Karunaratne and K.G. Upul Wijayantha 52

Floating-zone growth and characterization of triangular lattice antiferromagnetic α-SrCr₂O₄ crystals

L. Zhao, K.-J. Wang, M.-H. Wen and M.-K. Wu 81

Flux-Czochralski growth of Ca₉Y(VO₄)₇ crystal

S. Sun, L. Zhang, Y. Huang, Z. Lin and G. Wang 98

